

TAN 350

350 Watts, 50 Volts, Pulsed Avionics 960 – 1215 MHz

GENERAL DESCRIPTION

The **TAN350** is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 960-1215 MHz. The device has gold thin-film metallization and diffused ballasting for proven highest MTTF. The transistor includes input and output prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

CASE OUTLINE 55ST Style 1

ABSOLUTE MAXIMUM RATINGS

Power Dissipation

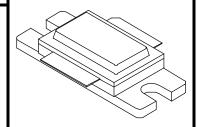
Device Dissipation @25°C (P_d) 1450 W (At rated pulse condition)

Voltage and Current

 $\begin{array}{lll} \mbox{Collector to Base Voltage } (BV_{ces}) & 65 \ V \\ \mbox{Emitter to Base Voltage } (BV_{ebo}) & 2.0 \ V \\ \mbox{Collector Current } (I_c) & 40 \ A \end{array}$

Temperatures

Storage Temperature $-65 \text{ to } +200 \text{ }^{\circ}\text{C}$ Operating Junction Temperature $+230 \text{ }^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS @ 25°C

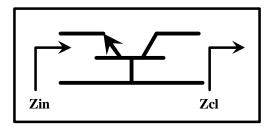
SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P _{out}	Power Out	F = 960 - 1215 MHz	350			W
P_{in}	Power Input	$V_{CC} = 50 \text{ Volts}$			70	W
P_{g}	Power Gain	$PW = 10 \mu sec$	7.0	7.5		dB
η_c	Collector Efficiency	DF = 10%	38	40		%
VSWR	Load Mismatch Tolerance	F = 1090 MHz	3:1			

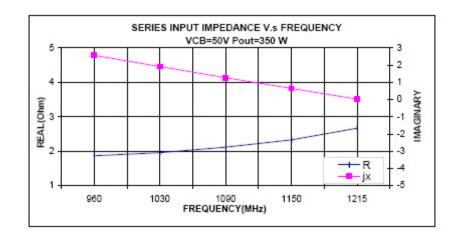
FUNCTIONAL CHARACTERISTICS @ 25°C

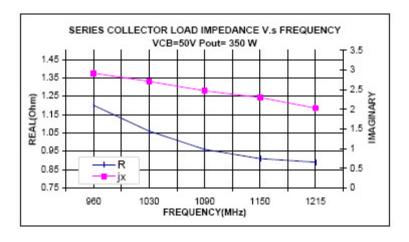
$\mathrm{BV}_{\mathrm{ebo}}$	Emitter to Base Breakdown	Ie = 25 mA	2.0		V
BV_{ces}	Collector to Emitter Breakdown	Ic = 50 mA	65		V
h_{FE}	DC – Current Gain	Ic = 1A, Vce = 5V	10		
θjc^2	Thermal Resistance			.12	°C/W

Rev A - Sept. 2005

	Zin		ZCL	
Frequency	R	jx	R	jx
960	1.87	2.58	1.2	2.92
1030	1.96	1.92	1.06	2.71
1090	2.12	1.27	0.96	2.47
1150	2.33	0.65	0.91	2.3
1215	2.67	0.03	0.89	2.03







Advanced Power Technology reserves the right to change, without notice, the specifications and information contained herein. Visit our web site at www.advancedpower.com or contact our factory direct.

